## MSKSEMI















**ESD** 

TVS

TSS

MOV

GDT

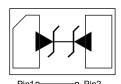
**PLED** 

# Broduct data sheet





#### **DFN1610-2L**



Marking D5N

#### **Feature**

- $\triangleright$  1500W Peak pulse power per line (t<sub>P</sub> = 8/20 $\mu$ s)
- DFN1610-2L package
- Response time is typically < 1 ns</p>
- Protect one I/O or power line
- Low clamping Voltage
- RoHS compliant
- > Transient protection for data lines to

IEC 61000-4-2(ESD) ±30KV(air), ±30KV(contact); IEC 61000-4-4 (EFT) 40A (5/50ns)

### **Applications**

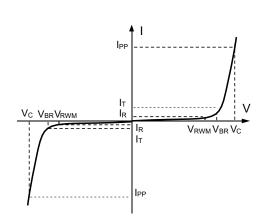
- Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- Notebooks, desktops, and servers
- Portable instrumentation
- Cordless phones
- Digital cameras
- Peripherals
- MP3 players

#### **Mechanical Characteristics**

- ➤ Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature:260°C
- ➤ Pure tin plating: 7 ~ 17 um
- ➤ Pin flatness:≤3mil
- Device meets MSL 3 requirements

#### **Electronics Parameter**

Symbol	Parameter	
V <sub>RWM</sub>	Peak Reverse Working Voltage	
I <sub>R</sub>	Reverse Leakage Current @ V <sub>RWM</sub>	
$V_{BR}$	Breakdown Voltage @ I <sub>⊺</sub>	
lτ	Test Current	
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current	
Vc	Clamping Voltage @ IPP	
P <sub>PP</sub>	Peak Pulse Power	
CJ	Junction Capacitance	





## Electrical characteristics per line@25℃ (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	V <sub>RWM</sub>				5.0	V
Breakdown Voltage	V <sub>BR</sub>	I <sub>t</sub> = 1mA	5.5		7.5	V
Reverse Leakage Current	IR	V <sub>RWM</sub> = 5V T=25°C			1.0	μA
Clamping Voltage	Vc	I <sub>PP</sub> =20A t <sub>P</sub> = 8/20µs		8.0	10	V
Clamping Voltage	Vc	I <sub>PP</sub> =50A t <sub>P</sub> = 8/20µs		9.0	11	V
Clamping Voltage	Vc	I <sub>PP</sub> =100A t <sub>P</sub> = 8/20µs		10	12	V
Clamping Voltage	Vc	I <sub>PP</sub> =140A t <sub>P</sub> = 8/20µs		11	13	V
Junction Capacitance	C <sub>j</sub>	V <sub>R</sub> =0V f = 1MHz		400	450	pF

#### Note

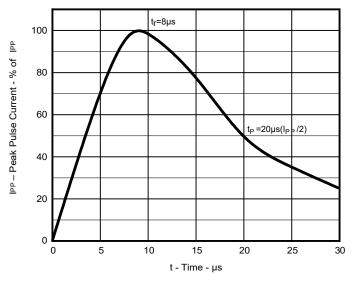
## Absolute maximum rating@25℃

Rating	Symbol	Value	Units
Peak Pulse Power ( t₂ = 8/20μs )	P <sub>PP</sub>	1500	W
Peak Pulse Current ( t <sub>P</sub> = 8/20μs )	<b>I</b> PP	140	А
Lead Soldering Temperature	T∟	260 (10 sec)	$^{\circ}$ C
Junction and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55~+150	$^{\circ}$ C

<sup>1)</sup> VRWM is the maximum reverse working voltage, or reverse stand-off voltage. ESD can protect signal line properly within its rated voltage. If the signal line's voltage is over VRWM, ESD will change to other state.



## **Typical Characteristics**



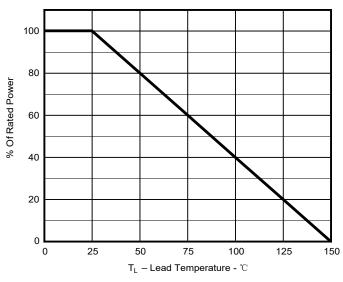
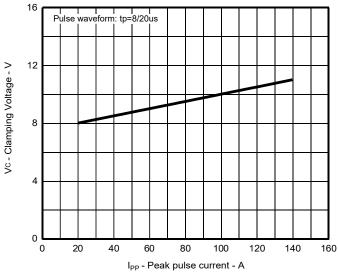


Fig 1.Pulse Waveform(8/20µs)

Fig 2.Power Derating Curve



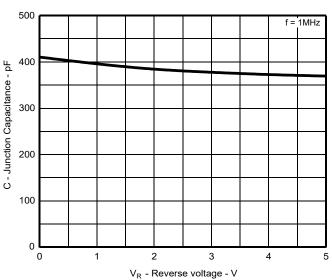


Fig 3. Clamping voltage vs. Peak pulse current

Fig 4. Capacitance vs. Reveres voltage

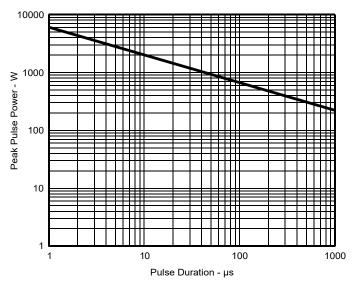


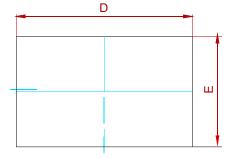
Fig 5. Non Repetitive Peak Pulse Power vs. Pulse time

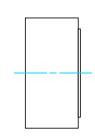


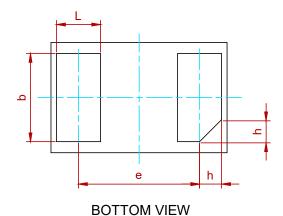
Semiconductor

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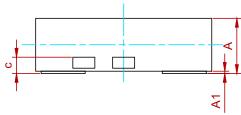
#### **PACKAGE MECHANICAL DATA**







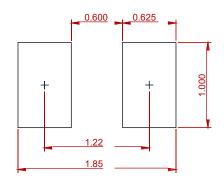
TOP VIEW



SIDE VIEW

Symbol	Dimensions in Millimeters			
	Min.	Тур.	Max.	
А	0.45	0.50	0.55	
A1	0.00	0.02	0.05	
С		0.15 Ref.		
b	0.75	0.80	0.85	
L	0.35	0.40	0.45	
D	1.55	1.60	1.65	
E	0.95	1.00	1.05	
е		1.10 BSC		
h		0.20 Ref.		

#### Recommend PCB Layout (Unit: mm)



#### Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
PTVSHC2EN5VB-MS	DFN1610-2L	3000



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